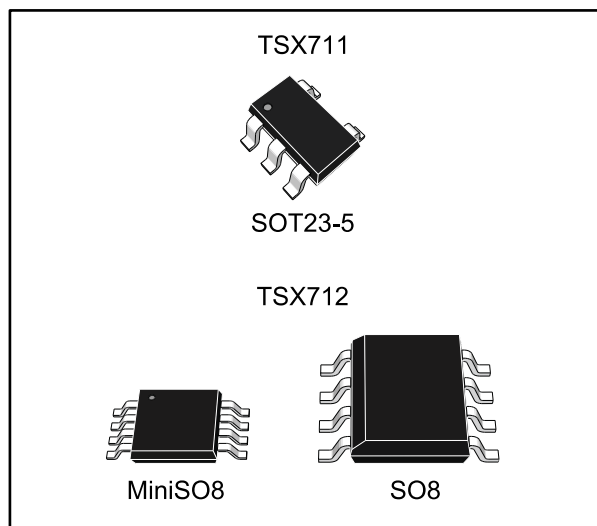


Low-power, precision, rail-to-rail, 2.7 MHz, 16 V CMOS operational amplifiers

Datasheet - production data



- See the TSX921 and TSX922 for higher speeds

Applications

- Battery-powered instrumentation
- Instrumentation amplifier
- Active filtering
- DAC buffer
- High-impedance sensor interface
- Current sensing (high and low side)

Description

The TSX711 and TSX712 series of operational amplifiers (op amps) offer high precision functioning with low input offset voltage down to a maximum of 200 μ V at 25 °C. In addition, their rail-to-rail input and output functionality allow these products to be used on full range input and output without limitation. This is particularly useful for a low-voltage supply such as 2.7 V that the TSX71x is able to operate with.

Thus, the TSX71x has the great advantage of offering a large span of supply voltages, ranging from 2.7 V to 16 V. They can be used in multiple applications with a unique reference.

Low input bias current performance makes the TSX71x perfect when used for signal conditioning in sensor interface applications. In addition, low-side and high-side current measurements can be easily made thanks to rail-to-rail functionality.

High ESD tolerance (4 kV HBM) and a wide temperature range are also good arguments to use the TSX71x in the automotive market segment.

Features

- Low input offset voltage: 200 μ V max.
- Rail-to-rail input and output
- Low current consumption: 800 μ A max.
- Gain bandwidth product: 2.7 MHz
- Low supply voltage: 2.7 - 16 V
- Unity gain stable
- Low input bias current: 50 pA max.
- High ESD tolerance: 4 kV HBM
- Extended temp. range: -40 °C to 125 °C
- Automotive qualification

Related products

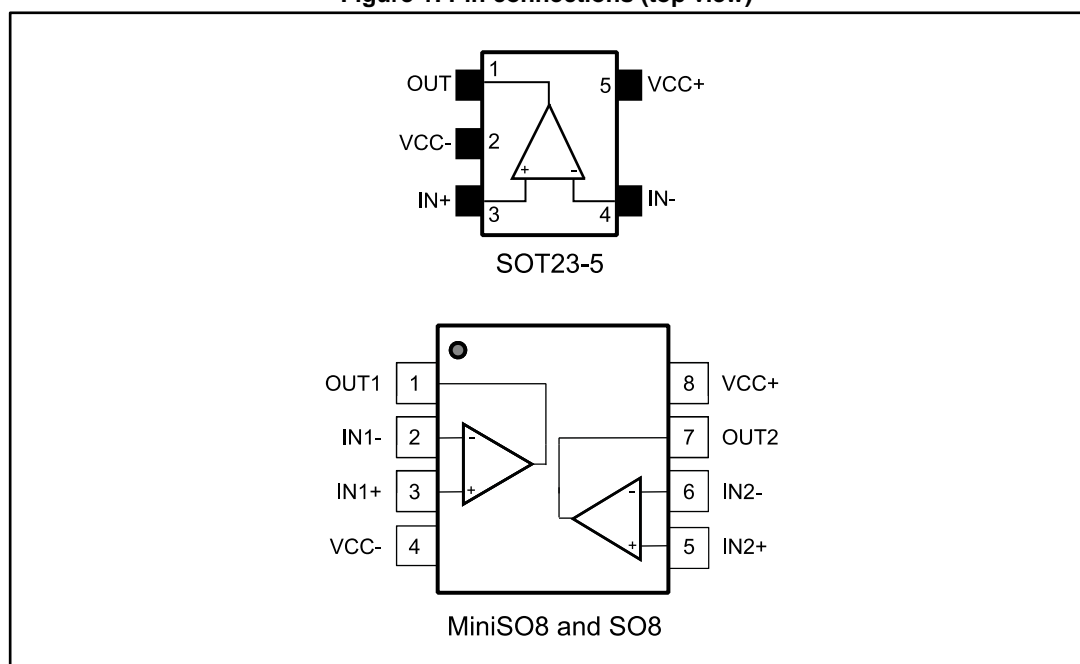
- See the TSX7191 and TSX7192 for higher speeds with similar precision
- See the TSX561 and TSX562 for low-power features
- See the TSX631 and TSX632 for micro-power features

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1 Package pin connections

Figure 1: Pin connections (top view)



2 Absolute maximum ratings and operating conditions

Table 1: Absolute maximum ratings (AMR)

Symbol	Parameter		Value	Unit
V_{CC}	Supply voltage ⁽¹⁾		18	V
V_{id}	Differential input voltage ⁽²⁾		$\pm V_{CC}$	mV
V_{in}	Input voltage		$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$	V
I_{in}	Input current ⁽³⁾		10	mA
T_{stg}	Storage temperature		-65 to 150	°C
R_{thja}	Thermal resistance junction to ambient ⁽⁴⁾⁽⁵⁾	SOT23-5	250	°C/W
		MiniSO8	190	
		SO8	125	
T_j	Maximum junction temperature		150	°C
ESD	HBM: human body model ⁽⁶⁾		4000	V
	MM: machine model ⁽⁷⁾		100	
	CDM: charged device model ⁽⁸⁾		1500	
	Latch-up immunity		200	mA

Notes:

- ⁽¹⁾ All voltage values, except the differential voltage are with respect to the network ground terminal.
- ⁽²⁾ Differential voltages are the non-inverting input terminal with respect to the inverting input terminal. See [Section 5.7](#) for the precautions to follow when using the TSX711 and TSX712 with a high differential input voltage.
- ⁽³⁾ Input current must be limited by a resistor in series with the inputs.
- ⁽⁴⁾ R_{th} are typical values.
- ⁽⁵⁾ Short-circuits can cause excessive heating and destructive dissipation.
- ⁽⁶⁾ According to JEDEC standard JESD22-A114F.
- ⁽⁷⁾ According to JEDEC standard JESD22-A115A.
- ⁽⁸⁾ According to ANSI/ESD STM5.3.1

Table 2: Operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	2.7 to 16	V
V_{icm}	Common mode input voltage range	$(V_{CC-}) - 0.1$ to $(V_{CC+}) + 0.1$	
T_{oper}	Operating free air temperature range	-40 to 125	°C

3 Electrical characteristics

Table 3: Electrical characteristics at $V_{CC+} = 4\text{ V}$ with $V_{CC-} = 0\text{ V}$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25\text{ }^{\circ}\text{C}$, and $R_L > 10\text{ k}\Omega$ connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{io} (TSX711, TSX712)	Input offset voltage	V _{icm} = V _{CC} /2			200	μV
		T _{min} < T _{op} < 85 °C			365	
		T _{min} < T _{op} < 125 °C			450	
V _{io} (TSX711A)		V _{icm} = V _{CC} /2			100	
		T _{min} < T _{op} < 85 °C			265	
		T _{min} < T _{op} < 125 °C			350	
ΔV _{io} /ΔT	Input offset voltage drift ⁽¹⁾				2.5	μV/°C
ΔV _{io}	Long term input offset voltage drift ⁽²⁾	T = 25 °C		1		$\frac{\text{nV}}{\sqrt{\text{month}}}$
I _{ib}	Input bias current ⁽¹⁾	V _{out} = V _{CC} /2		1	50	pA
		T _{min} < T _{op} < T _{max}			200	
I _{io}	Input offset current ⁽¹⁾	V _{out} = V _{CC} /2		1	50	
		T _{min} < T _{op} < T _{max}			200	
R _{IN}	Input resistance			1		TΩ
C _{IN}	Input capacitance			12.5		pF
CMRR (TSX711)	Common mode rejection ratio 20 log (ΔV _{ic} /ΔV _{io})	V _{icm} = -0.1 to 4.1 V, V _{out} = V _{CC} /2	84	102		dB
		T _{min} < T _{op} < T _{max}	83			
		V _{icm} = -0.1 to 2 V, V _{out} = V _{CC} /2	100	122		
		T _{min} < T _{op} < T _{max}	94			
CMRR (TSX712)		V _{icm} = -0.1 to 4.1 V, V _{out} = V _{CC} /2	80	98		
		T _{min} < T _{op} < T _{max}	78			
		V _{icm} = -0.1 to 2 V, V _{out} = V _{CC} /2	91	103		
		T _{min} < T _{op} < T _{max}	86			
A _{vd}	Large signal voltage gain	R _L = 2 kΩ, V _{out} = 0.3 to 3.7 V	110	136		
		T _{min} < T _{op} < T _{max}	96			
		R _L = 10 kΩ, V _{out} = 0.2 to 3.8 V	110	140		
		T _{min} < T _{op} < T _{max}	96			
V _{OH}	High level output voltage (voltage drop from V _{CC+})	R _L = 2 kΩ to V _{CC} /2		28	50	mV
		T _{min} < T _{op} < T _{max}			60	
		R _L = 10 kΩ to V _{CC} /2		6	15	
		T _{min} < T _{op} < T _{max}			20	

Electrical characteristics

TSX711, TSX712

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{OL}	Low level output voltage	$R_L = 2\text{ k}\Omega$ to $V_{CC}/2$		23	50	mV
		$T_{min} < T_{op} < T_{max}$			60	
		$R_L = 10\text{ k}\Omega$ to $V_{CC}/2$		5	15	
		$T_{min} < T_{op} < T_{max}$			20	
I_{out} (TSX711)	I_{sink}	$V_{out} = V_{CC}$	35	45		mA
		$T_{min} < T_{op} < T_{max}$	20			
	I_{source}	$V_{out} = 0\text{ V}$	35	45		
		$T_{min} < T_{op} < T_{max}$	20			
I_{out} (TSX712)	I_{sink}	$V_{out} = V_{CC}$	25	37		
		$T_{min} < T_{op} < T_{max}$	15			
	I_{source}	$V_{out} = 0\text{ V}$	35	45		
		$T_{min} < T_{op} < T_{max}$	20			
I_{CC}	Supply current per amplifier	No load, $V_{out} = V_{CC}/2$		570	800	μA
		$T_{min} < T_{op} < T_{max}$			900	
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	1.9	2.7		MHz
ϕ_m	Phase margin	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		50		Degrees
G_m	Gain margin	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		15		dB
SRn	Negative slew rate	$A_v = 1$, $V_{out} = 3\text{ V}_{PP}$, 10 % to 90 %	0.6	0.85		V/ μs
		$T_{min} < T_{op} < T_{max}$	0.5			
SRp	Positive slew rate	$A_v = 1$, $V_{out} = 3\text{ V}_{PP}$, 10 % to 90 %	1.0	1.4		
		$T_{min} < T_{op} < T_{max}$	0.9			
e_n	Equivalent input noise voltage	$f = 1\text{ kHz}$		22		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$
		$f = 10\text{ kHz}$		19		
THD+N	Total harmonic distortion + noise	$f = 1\text{ kHz}$, $A_v = 1$, $R_L = 10\text{ k}\Omega$, $BW = 22\text{ kHz}$, $V_{in} = 0.8\text{ V}_{PP}$		0.001		%

Notes:

⁽¹⁾Maximum values are guaranteed by design.

⁽²⁾Typical value is based on the V_{io} drift observed after 1000h at 125 °C extrapolated to 25 °C using the Arrhenius law and assuming an activation energy of 0.7 eV. The operational amplifier is aged in follower mode configuration (see [Section 5.6](#)).

Table 4: Electrical characteristics at $V_{CC+} = 10\text{ V}$ with $V_{CC-} = 0\text{ V}$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25\text{ }^{\circ}\text{C}$, and $R_L > 10\text{ k}\Omega$ connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{io} (TSX711, TSX712)	Input offset voltage	V _{icm} = V _{CC} /2			200	μV
		T _{min} < T _{op} < 85 °C			365	
		T _{min} < T _{op} < 125 °C			450	
V _{io} (TSX711A)		V _{icm} = V _{CC} /2			100	
		T _{min} < T _{op} < 85 °C			265	
		T _{min} < T _{op} < 125 °C			350	
ΔV _{io} /ΔT	Input offset voltage drift ⁽¹⁾				2.5	μV/°C
ΔV _{io}	Long term input offset voltage drift ⁽²⁾	T = 25 °C		25		$\frac{\text{nV}}{\sqrt{\text{month}}}$
I _{ib}	Input bias current ⁽¹⁾	V _{out} = V _{CC} /2		1	50	pA
		T _{min} < T _{op} < T _{max}			200	
I _{io}	Input offset current ⁽¹⁾	V _{out} = V _{CC} /2		1	50	
		T _{min} < T _{op} < T _{max}			200	
R _{IN}	Input resistance			1		TΩ
C _{IN}	Input capacitance			12.5		pF
CMRR (TSX711)	Common mode rejection ratio 20 log (ΔV _{ic} /ΔV _{io})	V _{icm} = -0.1 to 10.1 V, V _{out} = V _{CC} /2	90	102		dB
		T _{min} < T _{op} < T _{max}	86			
		V _{icm} = -0.1 to 8 V, V _{out} = V _{CC} /2	105	117		
		T _{min} < T _{op} < T _{max}	95			
CMRR (TSX712)		V _{icm} = -0.1 to 10.1 V, V _{out} = V _{CC} /2	88	100		
		T _{min} < T _{op} < T _{max}	84			
		V _{icm} = -0.1 to 8 V, V _{out} = V _{CC} /2	98	106		
		T _{min} < T _{op} < T _{max}	92			
A _{vd}	Large signal voltage gain	R _L = 2 kΩ, V _{out} = 0.3 to 9.7 V	110	140		
		T _{min} < T _{op} < T _{max}	100			
		R _L = 10 kΩ, V _{out} = 0.2 to 9.8 V	110			
		T _{min} < T _{op} < T _{max}	100			
V _{OH}	High level output voltage (voltage drop from V _{CC+})	R _L = 2 kΩ o V _{CC} /2		45	70	mV
		T _{min} < T _{op} < T _{max}			80	
		R _L = 10 kΩ o V _{CC} /2		10	30	
		T _{min} < T _{op} < T _{max}			40	
V _{OL}	Low level output voltage	R _L = 2 kΩ o V _{CC} /2		42	70	
		T _{min} < T _{op} < T _{max}			80	
		R _L = 10 kΩ o V _{CC} /2		9	30	
		T _{min} < T _{op} < T _{max}			40	

Electrical characteristics

TSX711, TSX712

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_{out} (TSX711)	I_{sink}	$V_{out} = V_{CC}$	50	70		mA
		$T_{min} < T_{op} < T_{max}$	40			
	I_{source}	$V_{out} = 0\text{ V}$	50	69		
		$T_{min} < T_{op} < T_{max}$	40			
I_{out} (TSX712)	I_{sink}	$V_{out} = V_{CC}$	30	39		
		$T_{min} < T_{op} < T_{max}$	15			
	I_{source}	$V_{out} = 0\text{ V}$	50	69		
		$T_{min} < T_{op} < T_{max}$	40			
I_{CC}	Supply current per amplifier	No load, $V_{out} = V_{CC}/2$		630	850	μA
		$T_{min} < T_{op} < T_{max}$			1000	
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	1.9	2.7		MHz
ϕ_m	Phase margin	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		53		Degrees
G_m	Gain margin	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		15		dB
SRn	Negative slew rate	$A_v = 1$, $V_{out} = 8\text{ V}_{PP}$, 10 % to 90 %	0.8	1		V/ μs
		$T_{min} < T_{op} < T_{max}$	0.7			
SRp	Positive slew rate	$A_v = 1$, $V_{out} = 8\text{ V}_{PP}$, 10 % to 90 %	1.0	1.3		
		$T_{min} < T_{op} < T_{max}$	0.9			
e_n	Equivalent input noise voltage	$f = 1\text{ kHz}$		22		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$
		$f = 10\text{ kHz}$		19		
THD+N	Total harmonic distortion + noise	$f = 1\text{ kHz}$, $A_v = 1$, $R_L = 10\text{ k}\Omega$, $BW = 22\text{ kHz}$, $V_{in} = 5\text{ V}_{PP}$		0.0003		%

Notes:

⁽¹⁾Maximum values are guaranteed by design.

⁽²⁾Typical value is based on the V_{io} drift observed after 1000h at 125 °C extrapolated to 25 °C using the Arrhenius law and assuming an activation energy of 0.7 eV. The operational amplifier is aged in follower mode configuration (see [Section 5.6](#)).

Table 5: Electrical characteristics at $V_{CC+} = 16\text{ V}$ with $V_{CC-} = 0\text{ V}$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25\text{ °C}$, and $R_L > 10\text{ k}\Omega$ connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{io} (TSX711, TSX712)	Input offset voltage	V _{icm} = V _{CC} /2			200	μV
		T _{min} < T _{op} < 85 °C			365	
		T _{min} < T _{op} < 125 °C			450	
V _{io} (TSX711A)		V _{icm} = V _{CC} /2			100	
		T _{min} < T _{op} < 85 °C			265	
		T _{min} < T _{op} < 125 °C			350	
ΔV _{io} /ΔT	Input offset voltage drift ⁽¹⁾				2.5	μV/°C
ΔV _{io}	Long term input offset voltage drift ⁽²⁾	T = 25 °C		500		$\frac{\text{nV}}{\sqrt{\text{month}}}$
I _{ib}	Input bias current ⁽¹⁾	V _{out} = V _{CC} /2		1	50	pA
		T _{min} < T _{op} < T _{max}			200	
I _{io}	Input offset current ⁽¹⁾	V _{out} = V _{CC} /2		1	50	
		T _{min} < T _{op} < T _{max}			200	
R _{IN}	Input resistance			1		TΩ
C _{IN}	Input capacitance			12.5		pF
CMRR (TSX711)	Common mode rejection ratio 20 log (ΔV _{ic} /ΔV _{io})	V _{icm} = -0.1 to 16.1 V, V _{out} = V _{CC} /2	94	113		dB
		T _{min} < T _{op} < T _{max}	90			
		V _{icm} = -0.1 to 14 V, V _{out} = V _{CC} /2	110	116		
		T _{min} < T _{op} < T _{max}	96			
CMRR (TSX712)		V _{icm} = -0.1 to 16.1 V, V _{out} = V _{CC} /2	94	107		
		T _{min} < T _{op} < T _{max}	90			
		V _{icm} = -0.1 to 14 V, V _{out} = V _{CC} /2	100	107		
		T _{min} < T _{op} < T _{max}	90			
SVRR	Supply voltage rejection ratio 20 log (ΔV _{cc} /ΔV _{io})	V _{cc} = 4 to 16 V	100	131		
		T _{min} < T _{op} < T _{max}	90			
A _{vd}	Large signal voltage gain	R _L = 2 kΩ, V _{out} = 0.3 to 15.7 V	110	146		
		T _{min} < T _{op} < T _{max}	100			
		R _L = 10 kΩ, V _{out} = 0.2 to 15.8 V	110	149		
		T _{min} < T _{op} < T _{max}	100			

Electrical characteristics

TSX711, TSX712

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{OH}	High level output voltage (voltage drop from V_{CC+})	$R_L = 2\text{ k}\Omega$ (TSX711)		100	130	mV
		$R_L = 2\text{ k}\Omega$ (TSX712)		70	130	
		$T_{min} < T_{op} < T_{max}$			150	
		$R_L = 10\text{ k}\Omega$		16	40	
		$T_{min} < T_{op} < T_{max}$			50	
V_{OL}	Low level output voltage	$R_L = 2\text{ k}\Omega$		70	130	mV
		$T_{min} < T_{op} < T_{max}$			150	
		$R_L = 10\text{ k}\Omega$		15	40	
		$T_{min} < T_{op} < T_{max}$			50	
I_{out} (TSX711)	I_{sink}	$V_{out} = V_{CC}$	50	71		mA
		$T_{min} < T_{op} < T_{max}$	45			
	I_{source}	$V_{out} = 0\text{ V}$	50	68		
		$T_{min} < T_{op} < T_{max}$	45			
I_{out} (TSX712)	I_{sink}	$V_{out} = V_{CC}$	30	40		
		$T_{min} < T_{op} < T_{max}$	15			
	I_{source}	$V_{out} = 0\text{ V}$	50	68		
		$T_{min} < T_{op} < T_{max}$	45			
I_{CC}	Supply current per amplifier	No load, $V_{out} = V_{CC}/2$		660	900	μA
		$T_{min} < T_{op} < T_{max}$			1000	
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	1.9	2.7		MHz
ϕ_m	Phase margin	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		55		Degrees
G_m	Gain margin	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		15		dB
SRn	Negative slew rate	$A_v = 1$, $V_{out} = 10\text{ V}_{PP}$, 10 % to 90 %	0.7	0.95		V/ μs
		$T_{min} < T_{op} < T_{max}$	0.6			
SRp	Positive slew rate	$A_v = 1$, $V_{out} = 10\text{ V}_{PP}$, 10 % to 90 %	1	1.4		
		$T_{min} < T_{op} < T_{max}$	0.9			
e_n	Equivalent input noise voltage	$f = 1\text{ kHz}$		22		$\frac{nV}{\sqrt{Hz}}$
		$f = 10\text{ kHz}$		19		
THD+N	Total harmonic distortion + Noise	$f = 1\text{ kHz}$, $A_v = 1$, $R_L = 10\text{ k}\Omega$, $BW = 22\text{ kHz}$, $V_{in} = 10\text{ V}_{PP}$		0.0002		%

Notes:

⁽¹⁾Maximum values are guaranteed by design.

⁽²⁾Typical value is based on the V_{io} drift observed after 1000h at 125 °C extrapolated to 25 °C using the Arrhenius law and assuming an activation energy of 0.7 eV. The operational amplifier is aged in follower mode configuration (see [Section 5.6](#)).

4 Electrical characteristic curves

Figure 2: Supply current vs. supply voltage

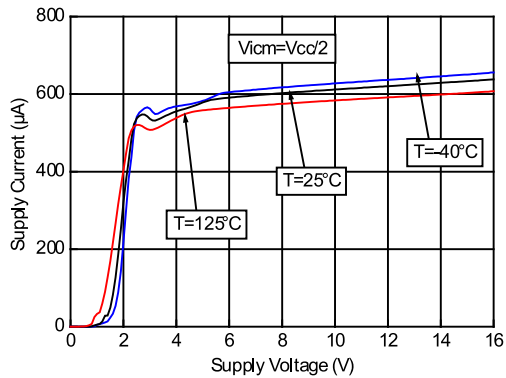


Figure 3: Input offset voltage distribution at VCC = 16 V

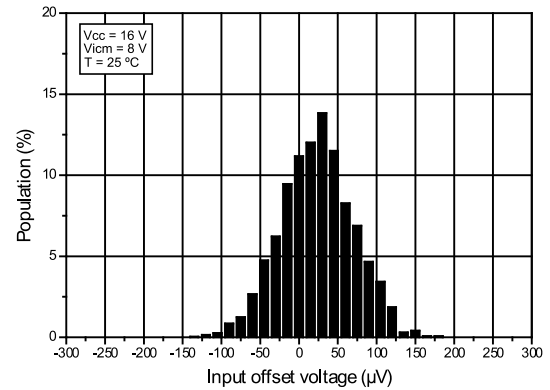


Figure 4: Input offset voltage distribution at VCC = 4 V

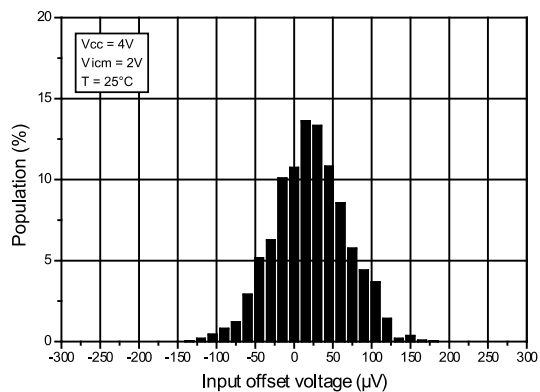


Figure 5: Input offset voltage vs. temperature at VCC = 16 V

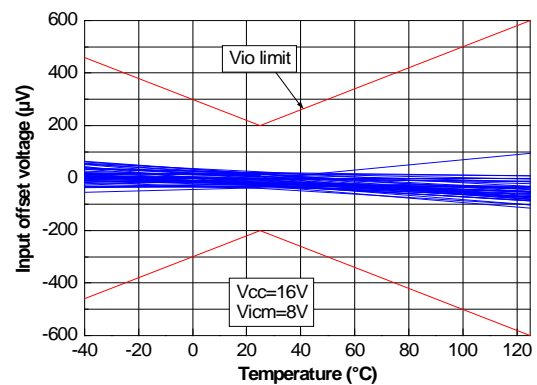


Figure 6: Input offset voltage drift population

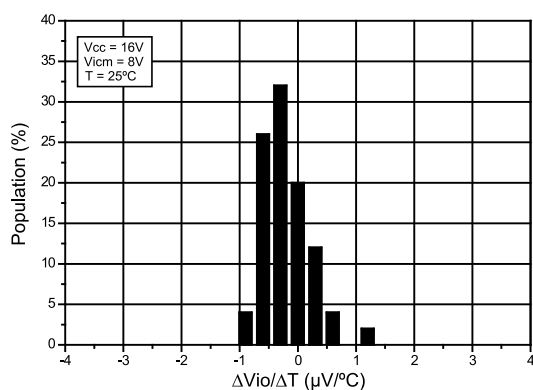


Figure 7: Input offset voltage vs. supply voltage at VICM = 0 V

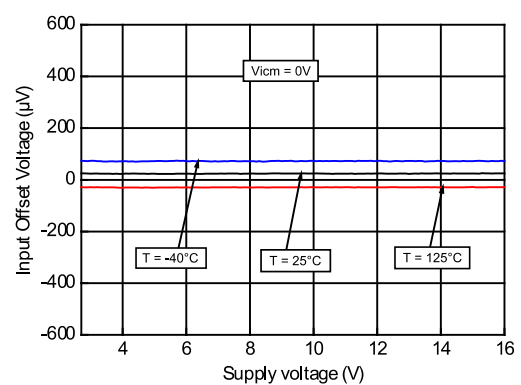


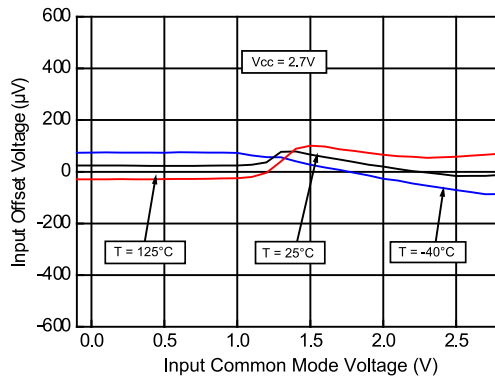
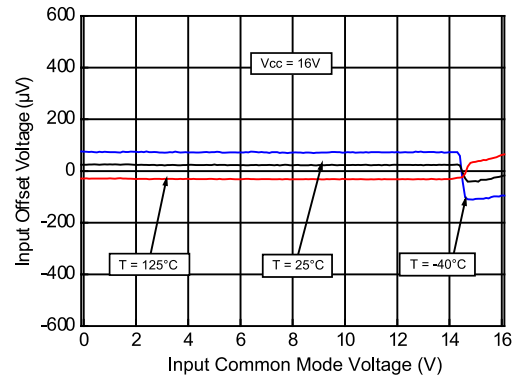
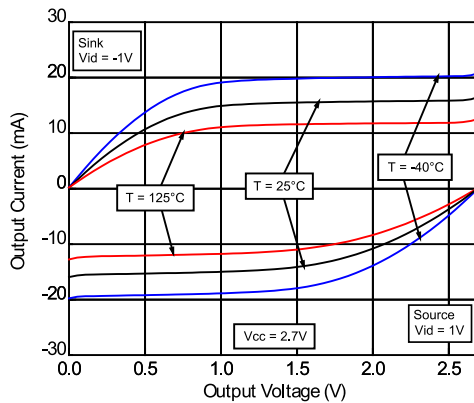
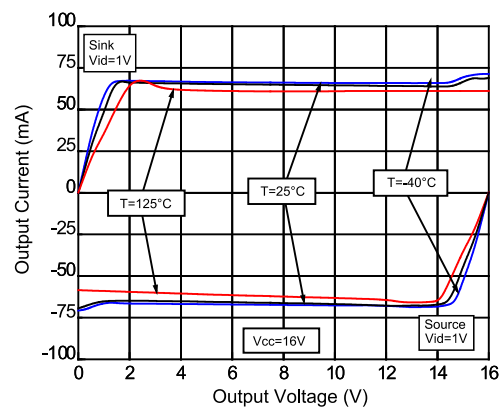
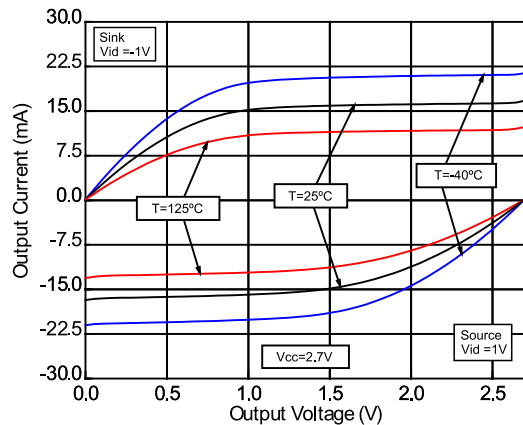
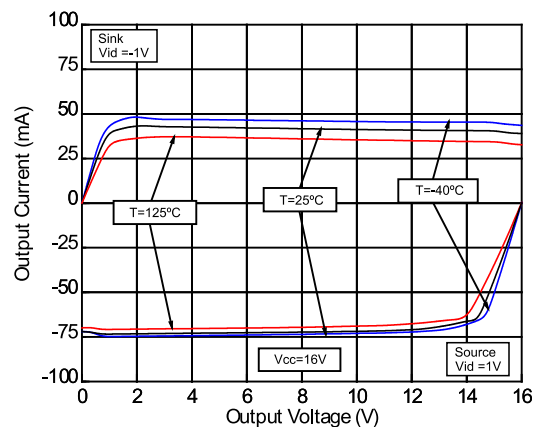
Figure 8: Input offset voltage vs. common mode voltage at $V_{CC} = 2.7\text{ V}$ Figure 9: Input offset voltage vs. common mode voltage at $V_{CC} = 16\text{ V}$ Figure 10: Output current vs. output voltage at $V_{CC} = 2.7\text{ V}$ (TSX711)Figure 11: Output current vs. output voltage at $V_{CC} = 16\text{ V}$ (TSX711)Figure 12: Output current vs. output voltage at $V_{CC} = 2.7\text{ V}$ (TSX712)Figure 13: Output current vs. output voltage at $V_{CC} = 16\text{ V}$ (TSX712)

Figure 14: Output low voltage vs. supply voltage

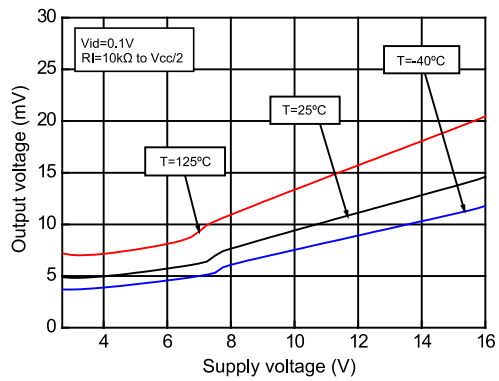


Figure 15: Output high voltage (drop from VCC+) vs. supply voltage

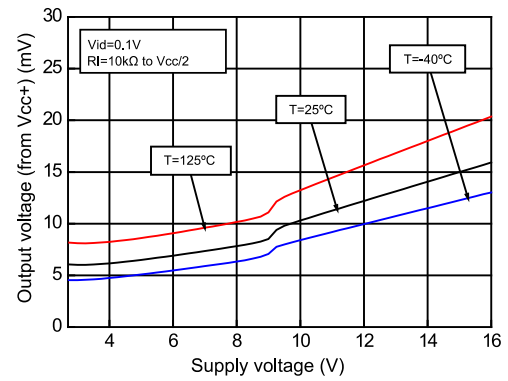


Figure 16: Output voltage vs. input voltage close to the rail at VCC = 16 V

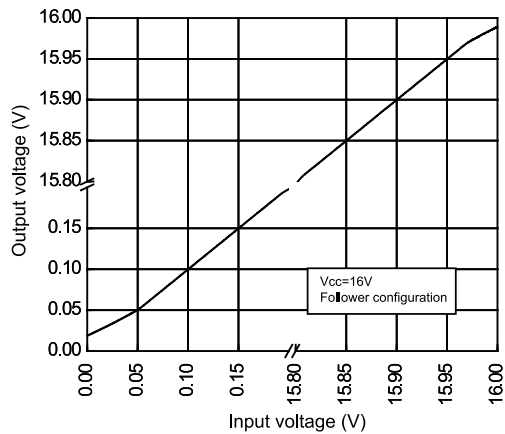


Figure 17: Slew rate vs. supply voltage

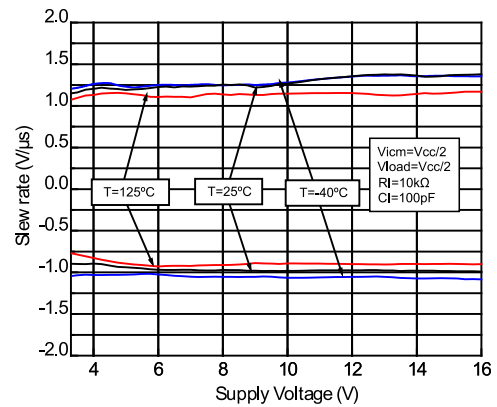


Figure 18: Negative slew rate at VCC = 16 V

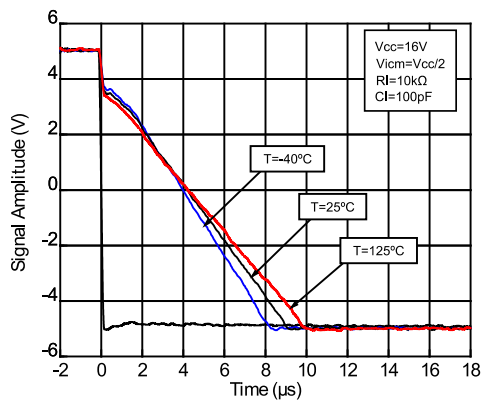


Figure 19: Positive slew rate at VCC = 16 V

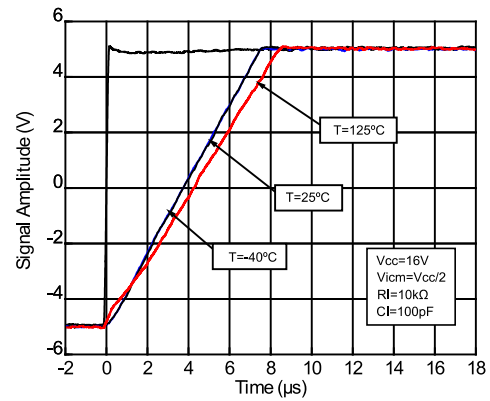


Figure 20: Response to a small input voltage step

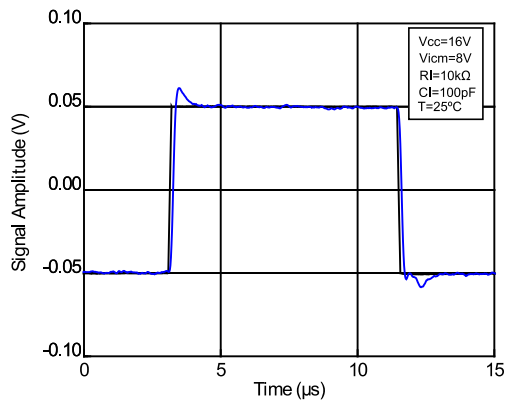


Figure 21: Recovery behavior after a negative step on the input

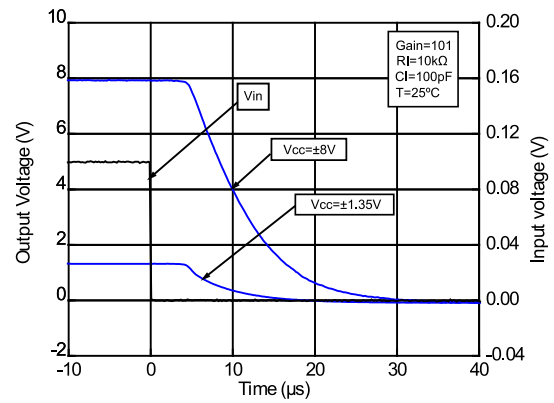


Figure 22: Recovery behavior after a positive step on the input

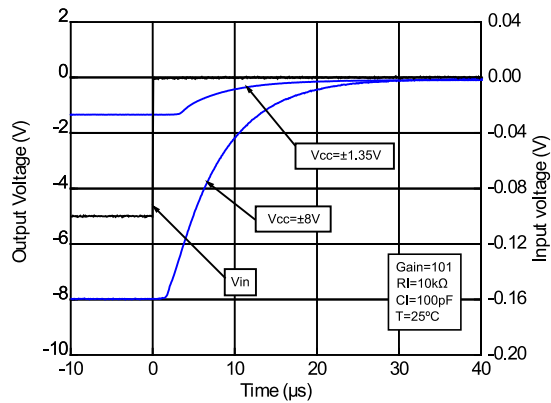
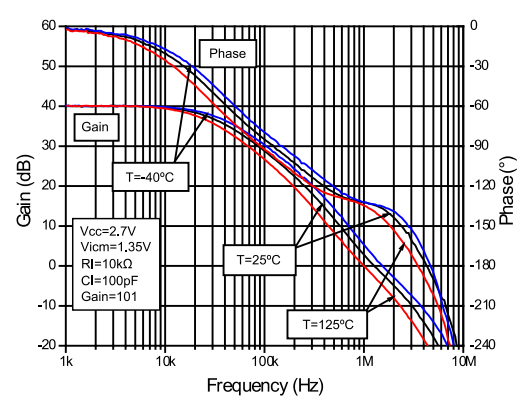
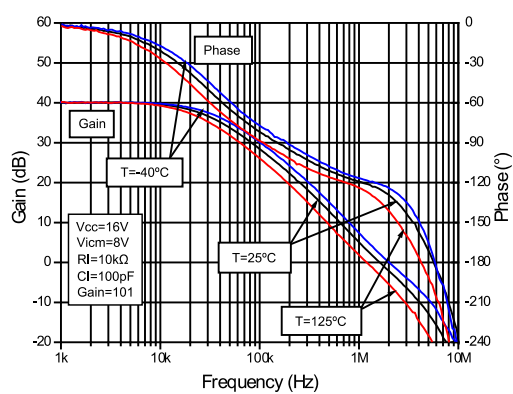
Figure 23: Bode diagram at $V_{CC} = 2.7V$ Figure 24: Bode diagram at $V_{CC} = 16V$ 

Figure 25: Power supply rejection ratio (PSRR) vs. frequency

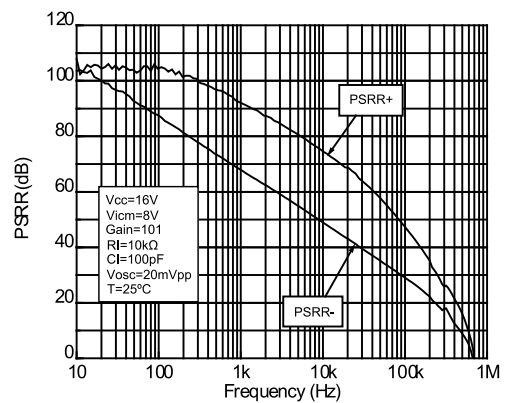


Figure 26: Output overshoot vs. capacitive load

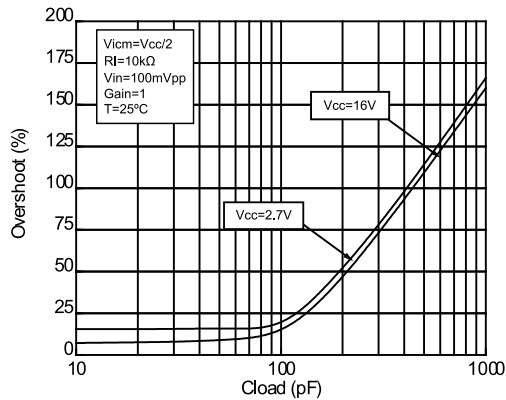


Figure 27: Output impedance vs. frequency in closed loop configuration

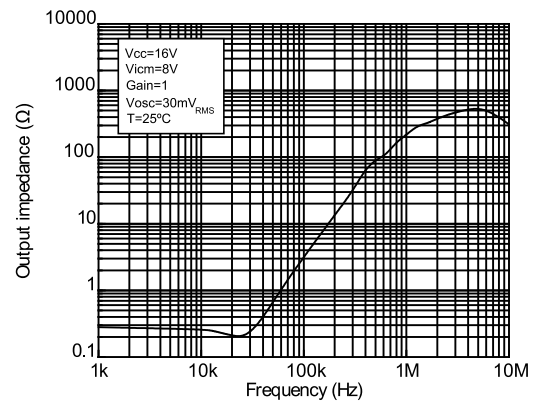


Figure 28: THD + N vs. frequency

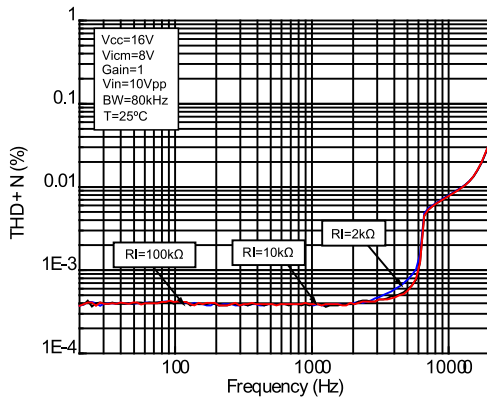


Figure 29: THD + N vs. output voltage

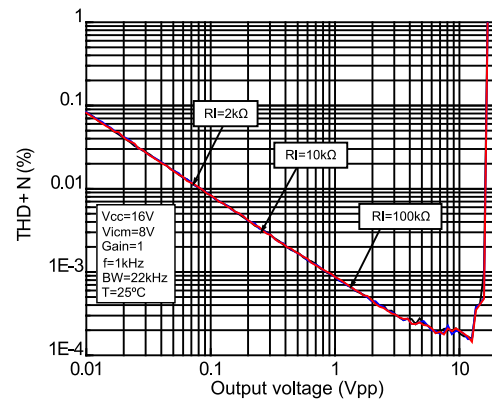


Figure 30: Noise vs. frequency

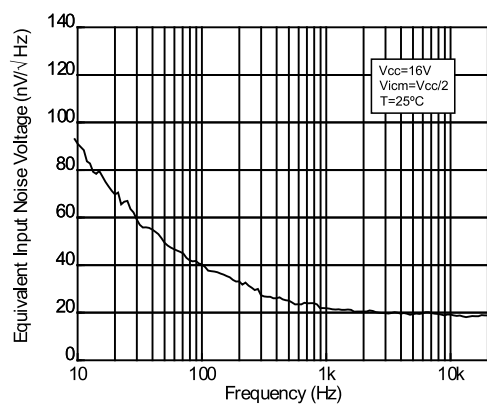


Figure 31: 0.1 to 10Hz noise

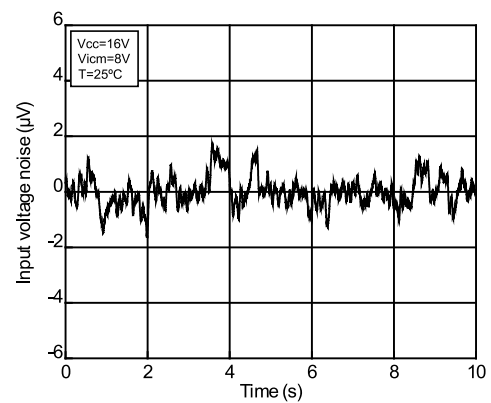
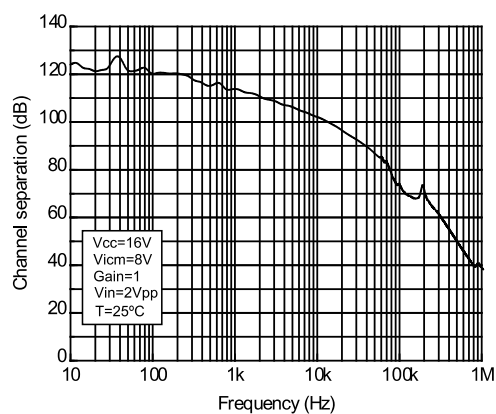


Figure 32: Channel separation (TSX712)



5 Application information

5.1 Operating voltages

The TSX711 and TSX712 devices can operate from 2.7 to 16 V. The parameters are fully specified for 4 V, 10 V, and 16 V power supplies. However, the parameters are very stable in the full V_{CC} range. Additionally, the main specifications are guaranteed in extended temperature ranges from -40 to 125 °C.

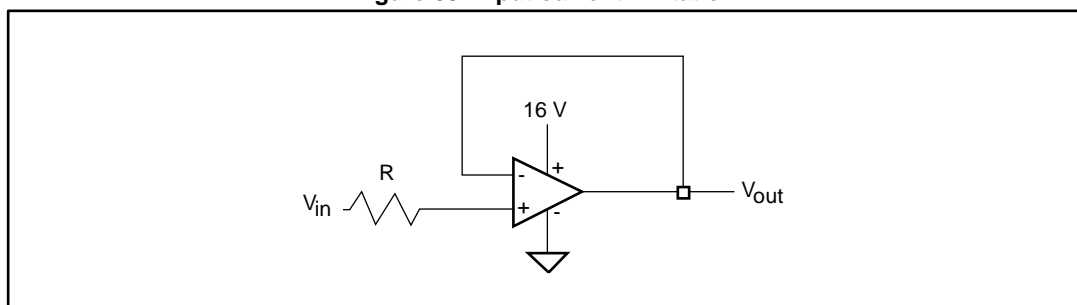
5.2 Input pin voltage ranges

The TSX711 and TSX712 devices have internal ESD diode protection on the inputs. These diodes are connected between the input and each supply rail to protect the input MOSFETs from electrical discharge.

If the input pin voltage exceeds the power supply by 0.5 V, the ESD diodes become conductive and excessive current can flow through them. Without limitation this over current can damage the device.

In this case, it is important to limit the current to 10 mA, by adding resistance on the input pin, as described in [Figure 33: "Input current limitation"](#).

Figure 33: Input current limitation



5.3 Rail-to-rail input

The TSX711 and TSX712 devices have a rail-to-rail input, and the input common mode range is extended from $(V_{CC-}) - 0.1$ V to $(V_{CC+}) + 0.1$ V.

5.4 Rail-to-rail output

The operational amplifier output levels can go close to the rails: to a maximum of 40 mV above and below the rail when connected to a 10 k Ω resistive load to $V_{CC}/2$.

5.5 Input offset voltage drift over temperature

The maximum input voltage drift variation over temperature is defined as the offset variation related to the offset value measured at 25 °C. The operational amplifier is one of the main circuits of the signal conditioning chain, and the amplifier input offset is a major contributor to the chain accuracy. The signal chain accuracy at 25 °C can be compensated during production at application level. The maximum input voltage drift over temperature enables the system designer to anticipate the effect of temperature variations.

The maximum input voltage drift over temperature is computed using [Equation 1](#).

Equation 1

$$\frac{\Delta V_{io}}{\Delta T} = \max \left| \frac{V_{io}(T) - V_{io}(25\text{ °C})}{T - 25\text{ °C}} \right|$$

Where T = -40 °C and 125 °C.

The TSX711 and TSX712 datasheet maximum values are guaranteed by measurements on a representative sample size ensuring a C_{pk} (process capability index) greater than 1.3.

5.6 Long term input offset voltage drift

To evaluate product reliability, two types of stress acceleration are used:

- Voltage acceleration, by changing the applied voltage
- Temperature acceleration, by changing the die temperature (below the maximum junction temperature allowed by the technology) with the ambient temperature.

The voltage acceleration has been defined based on JEDEC results, and is defined using [Equation 2](#).

Equation 2

$$A_{FV} = e^{\beta \cdot (V_S - V_U)}$$

Where:

A_{FV} is the voltage acceleration factor

β is the voltage acceleration constant in 1/V, constant technology parameter (β = 1)

V_S is the stress voltage used for the accelerated test

V_U is the voltage used for the application

The temperature acceleration is driven by the Arrhenius model, and is defined in [Equation 3](#).

Equation 3

$$A_{FT} = e^{\frac{E_a}{k} \cdot \left(\frac{1}{T_U} - \frac{1}{T_S} \right)}$$

Where:

A_{FT} is the temperature acceleration factor

E_a is the activation energy of the technology based on the failure rate

k is the Boltzmann constant ($8.6173 \times 10^{-5} \text{ eV.K}^{-1}$)

T_U is the temperature of the die when V_U is used (K)

T_S is the temperature of the die under temperature stress (K)

The final acceleration factor, A_F , is the multiplication of the voltage acceleration factor and the temperature acceleration factor ([Equation 4](#)).

Equation 4

$$A_F = A_{FT} \times A_{FV}$$

A_F is calculated using the temperature and voltage defined in the mission profile of the product. The A_F value can then be used in [Equation 5](#) to calculate the number of months of use equivalent to 1000 hours of reliable stress duration.

Equation 5

$$\text{Months} = A_F \times 1000 \text{ h} \times 12 \text{ months} / (24 \text{ h} \times 365.25 \text{ days})$$

To evaluate the op amp reliability, a follower stress condition is used where V_{CC} is defined as a function of the maximum operating voltage and the absolute maximum rating (as recommended by JEDEC rules).

The V_{io} drift (in μV) of the product after 1000 h of stress is tracked with parameters at different measurement conditions (see [Equation 6](#)).

Equation 6

$$V_{CC} = \max V_{op} \text{ with } V_{icm} = V_{CC} / 2$$

The long term drift parameter (ΔV_{io}), estimating the reliability performance of the product, is obtained using the ratio of the V_{io} (input offset voltage value) drift over the square root of the calculated number of months ([Equation 7](#)).

Equation 7

$$\Delta V_{io} = \frac{V_{io} \text{ drift}}{\sqrt{(\text{months})}}$$

Where V_{io} drift is the measured drift value in the specified test conditions after 1000 h stress duration.

5.7 High values of input differential voltage

In a closed loop configuration, which represents the typical use of an op amp, the input differential voltage is low (close to V_{io}). However, some specific conditions can lead to higher input differential values, such as:

- operation in an output saturation state
- operation at speeds higher than the device bandwidth, with output voltage dynamics limited by slew rate.
- use of the amplifier in a comparator configuration, hence in open loop

Use of the TSX711 or TSX712 in comparator configuration, especially combined with high temperature and long duration can create a permanent drift of V_{io} .

5.8 Capacitive load

Driving large capacitive loads can cause stability problems. Increasing the load capacitance produces gain peaking in the frequency response, with overshoot and ringing in the step response. It is usually considered that with a gain peaking higher than 2.3 dB an op amp might become unstable.

Generally, the unity gain configuration is the worst case for stability and the ability to drive large capacitive loads.

Figure 34: "Stability criteria with a serial resistor at different supply voltage" shows the serial resistor that must be added to the output, to make a system stable. *Figure 35: "Test configuration for Riso"* shows the test configuration using an isolation resistor, Riso.

Figure 34: Stability criteria with a serial resistor at different supply voltage

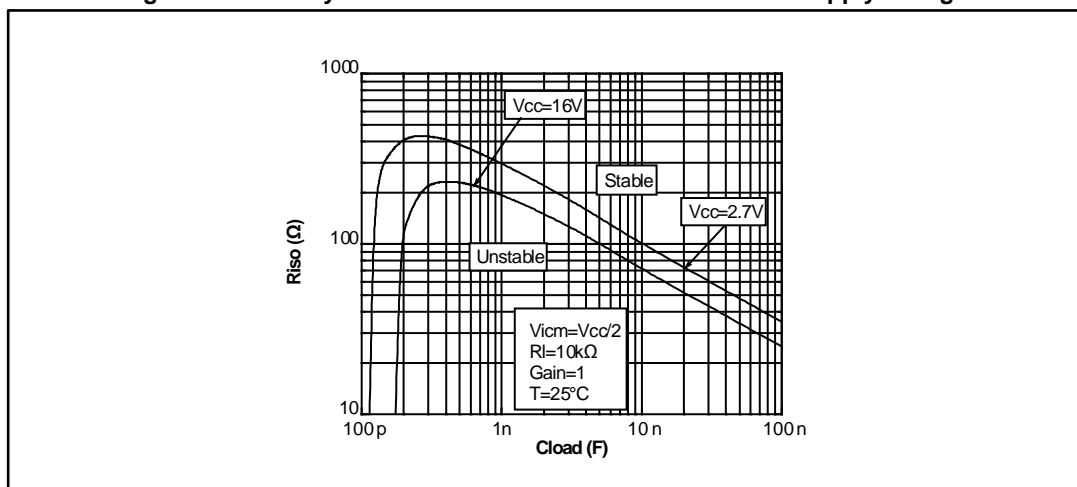
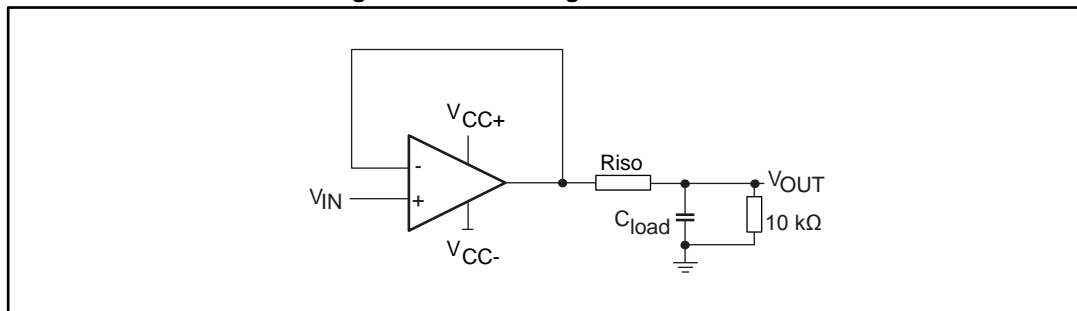


Figure 35: Test configuration for Riso



5.9 PCB layout recommendations

Particular attention must be paid to the layout of the PCB, tracks connected to the amplifier, load, and power supply. The power and ground traces are critical as they must provide adequate energy and grounding for all circuits. The best practice is to use short and wide PCB traces to minimize voltage drops and parasitic inductance.

In addition, to minimize parasitic impedance over the entire surface, a multi-via technique that connects the bottom and top layer ground planes together in many locations is often used.

The copper traces that connect the output pins to the load and supply pins should be as wide as possible to minimize trace resistance.

5.10 Optimized application recommendation

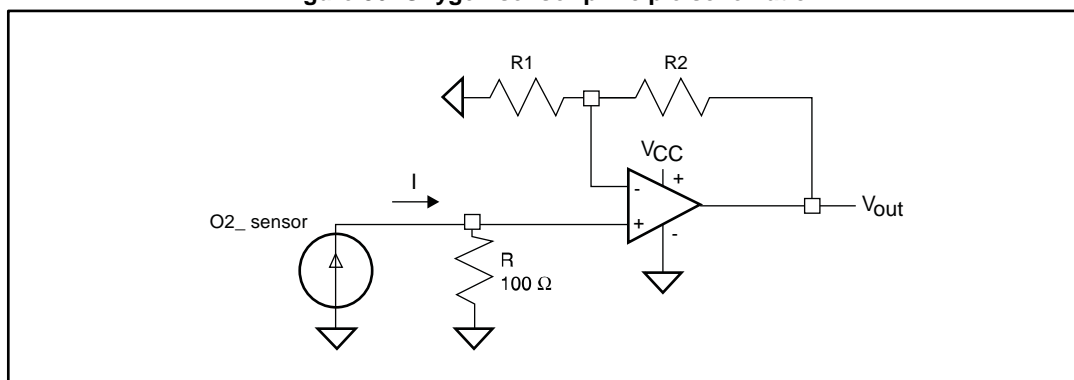
It is recommended to place a 22 nF capacitor as close as possible to the supply pin. A good decoupling will help to reduce electromagnetic interference impact.

5.11 Application examples

5.11.1 Oxygen sensor

The electrochemical sensor creates a current proportional to the concentration of the gas being measured. This current is converted into voltage thanks to R resistance. This voltage is then amplified by the TSX711 or the TSX712 (see [Figure 36: "Oxygen sensor principle schematic"](#)).

Figure 36: Oxygen sensor principle schematic



The output voltage is calculated using [Equation 8](#):

Equation 8

$$V_{out} = (I \times R - V_{io}) \times \left(\frac{R_2}{R_1} + 1 \right)$$

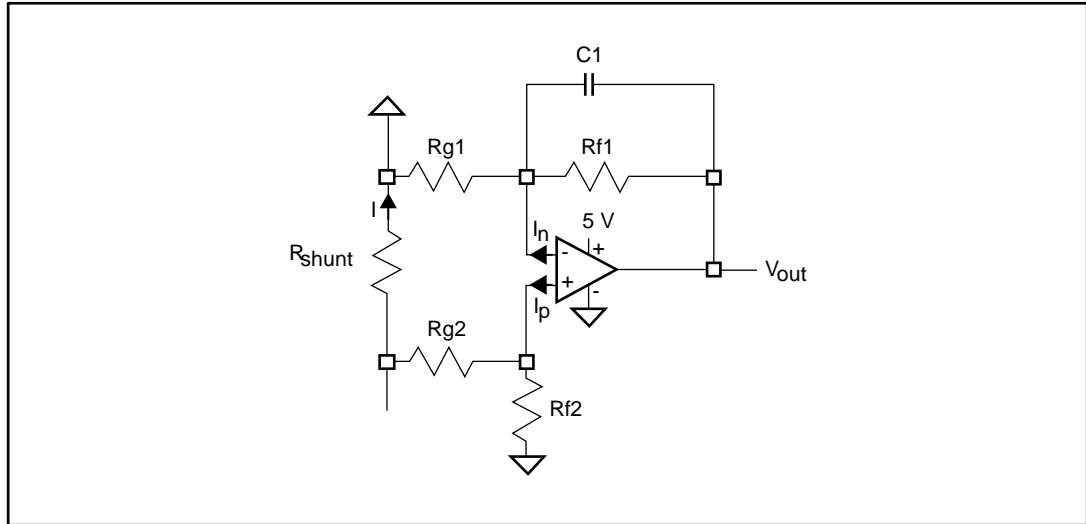
As the current delivered by the O2 sensor is extremely low, the impact of the V_{io} can become significant with a traditional operational amplifier. The use of a precision amplifier like the TSX711/TSX712 is perfect for this application.

In addition, using the TSX711/TSX712 for the O2 sensor application ensures that the measurement of O2 concentration is stable, even at different temperatures, thanks to a small $\Delta V_{io}/\Delta T$.

5.11.2 Low-side current sensing

Power management mechanisms are found in most electronic systems. Current sensing is useful for protecting applications. The low-side current sensing method consists of placing a sense resistor between the load and the circuit ground. The resulting voltage drop is amplified using the TSX711 or TSX712 (see [Figure 37: "Low-side current sensing schematic"](#)).

Figure 37: Low-side current sensing schematic



V_{out} can be expressed as follows:

Equation 9

$$V_{out} = R_{shunt} \times I \left(1 - \frac{R_{g2}}{R_{g2} + R_{f2}} \right) \left(1 + \frac{R_{f1}}{R_{g1}} \right) + I_p \left(\frac{R_{g2} \times R_{f2}}{R_{g2} + R_{f2}} \right) \times \left(1 + \frac{R_{f1}}{R_{g1}} \right) - I_n \times R_{f1} - V_{io} \left(1 + \frac{R_{f1}}{R_{g1}} \right)$$

Assuming that $R_{f2} = R_{f1} = R_f$ and $R_{g2} = R_{g1} = R_g$, [Equation 9](#) can be simplified as follows:

Equation 10

$$V_{out} = R_{shunt} \times I \left(\frac{R_f}{R_g} \right) - V_{io} \left(1 + \frac{R_f}{R_g} \right) + R_f \times I_{io}$$

The main advantage of using a precision amplifier like the TSX711 or TSX712, for a low-side current sensing, is that the errors due to V_{io} and I_{io} are extremely low and may be neglected.

Therefore, for the same accuracy, the shunt resistor can be chosen with a lower value, resulting in lower power dissipation, lower drop in the ground path, and lower cost.

Particular attention must be paid on the matching and precision of R_{g1} , R_{g2} , R_{f1} , and R_{f2} , to maximize the accuracy of the measurement.

Taking into consideration the resistor inaccuracies, the maximum and minimum output voltage of the operational amplifier can be calculated respectively using [Equation 11](#) and [Equation 12](#).

Equation 11

$$\text{Maximum } V_{out} = R_{shunt} \times I \times \left(\frac{R_f}{R_g} \right) \times (1 + \varepsilon_{rs} + 2\varepsilon_r) + V_{io} \times \left(1 + \frac{R_f}{R_g} \right) + R_f \times I_{io}$$

Equation 12

$$\text{Minimum } V_{out} = R_{shunt} \times I \times \left(\frac{R_f}{R_g} \right) \times (1 - \varepsilon_{rs} - 2\varepsilon_r) - V_{io} \times \left(1 + \frac{R_f}{R_g} \right) + R_f \times I_{io}$$

Where:

- ε_{rs} is the shunt resistor inaccuracy (example, 1 %)
- ε_r is the inaccuracy of the R_f and R_g resistors (example, 0.1 %)

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK[®] is an ST trademark.

6.1 SOT23-5 package information

Figure 38: SOT23-5 package outline

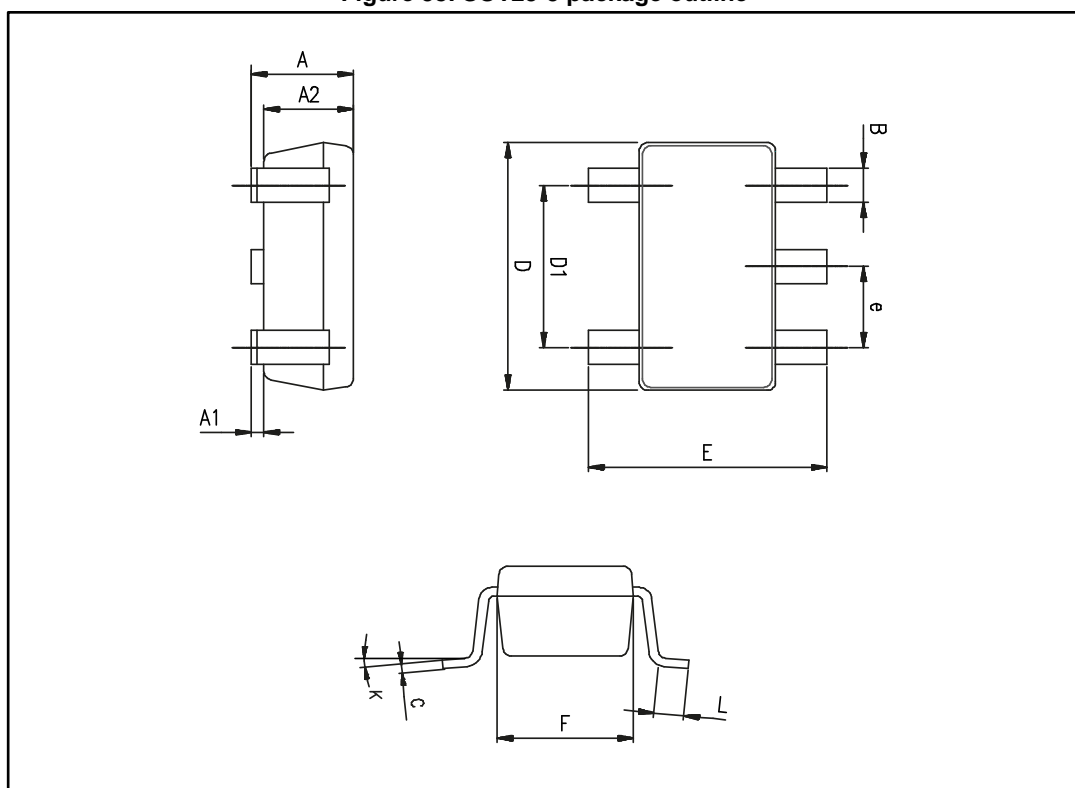


Table 6: SOT23-5 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.90	1.20	1.45	0.035	0.047	0.057
A1			0.15			0.006
A2	0.90	1.05	1.30	0.035	0.041	0.051
B	0.35	0.40	0.50	0.014	0.016	0.020
C	0.09	0.15	0.20	0.004	0.006	0.008
D	2.80	2.90	3.00	0.110	0.114	0.118
D1		1.90			0.075	
e		0.95			0.037	
E	2.60	2.80	3.00	0.102	0.110	0.118
F	1.50	1.60	1.75	0.059	0.063	0.069
L	0.10	0.35	0.60	0.004	0.014	0.024
K	0 degrees		10 degrees	0 degrees		10 degrees

6.2 MiniSO8 package information

Figure 39: MiniSO8 package outline

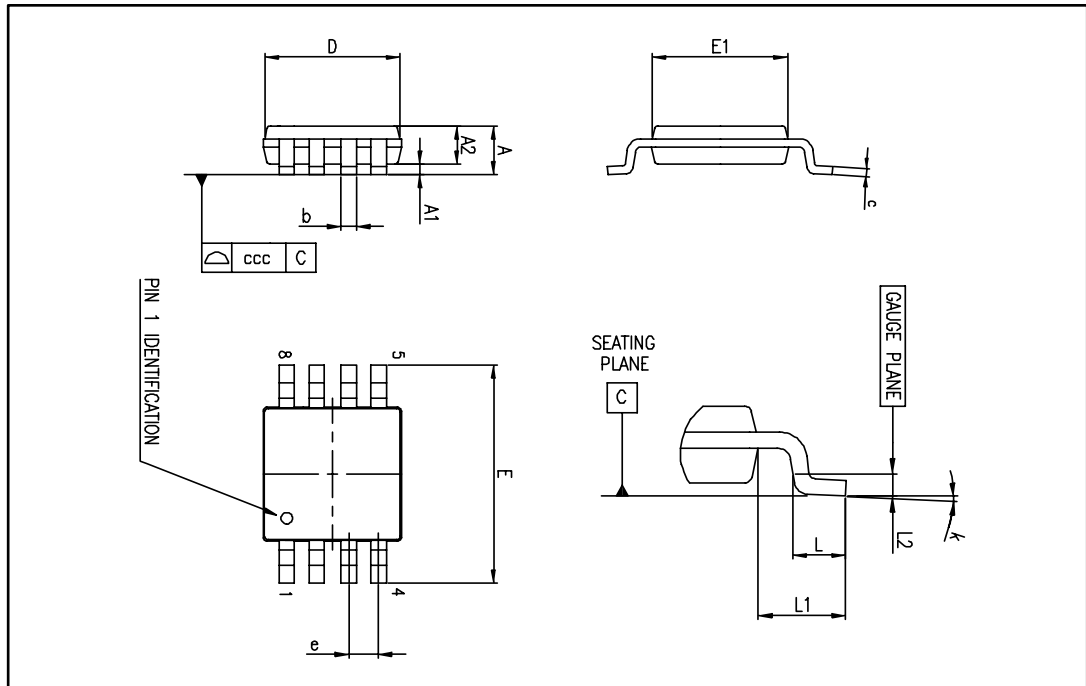


Table 7: MiniSO8 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.1			0.043
A1	0		0.15	0		0.006
A2	0.75	0.85	0.95	0.030	0.033	0.037
b	0.22		0.40	0.009		0.016
c	0.08		0.23	0.003		0.009
D	2.80	3.00	3.20	0.11	0.118	0.126
E	4.65	4.90	5.15	0.183	0.193	0.203
E1	2.80	3.00	3.10	0.11	0.118	0.122
e		0.65			0.026	
L	0.40	0.60	0.80	0.016	0.024	0.031
L1		0.95			0.037	
L2		0.25			0.010	
k	0°		8°	0°		8°
ccc			0.10			0.004

6.3 SO8 package information

Figure 40: SO8 package outline

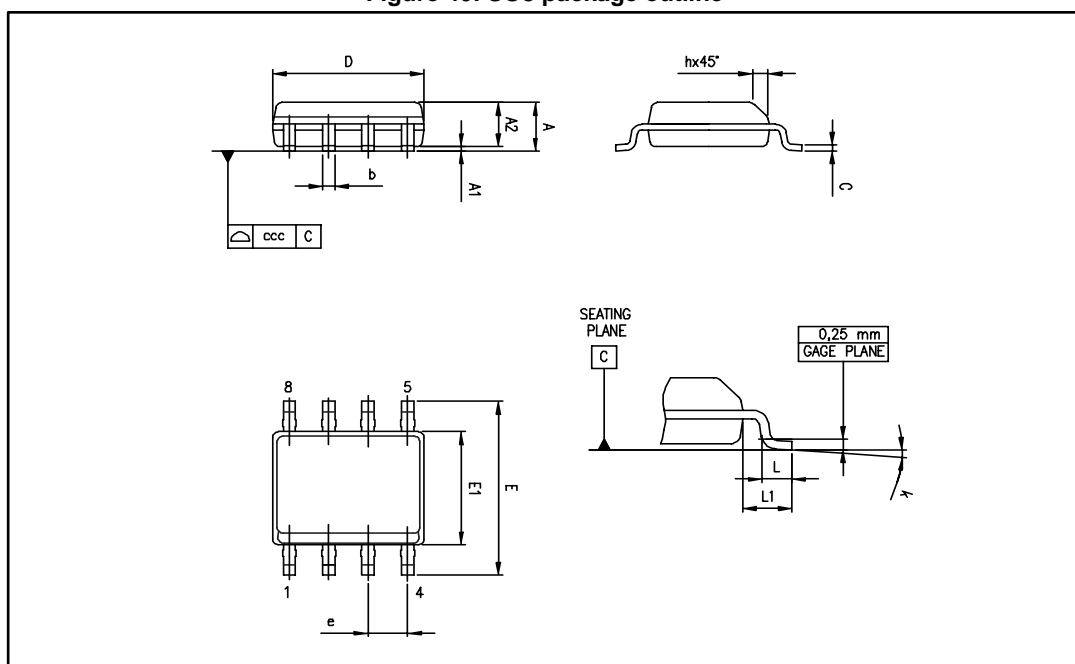


Table 8: SO8 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max
A			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
c	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
L1		1.04			0.040	
k	1°		8°	1°		8°
CCC			0.10			0.004

7 Ordering information

Table 9: Order codes

Order code	Temperature range	Package	Packaging	Marking
TSX711ILT	-40 to 125 °C	SOT23-5	Tape and reel	K29
TSX711AILT				K195
TSX711IYLT ⁽¹⁾	-40 to 125 °C (automotive grade)			K197
TSX711AIYLT ⁽¹⁾				K198
TSX712IDT	-40 to 125 °C	SO8		TSX712
TSX712IST		MiniSO8		K211
TSX712IYDT ⁽²⁾	-40 to 125 °C (automotive grade)	SO8		TSX712Y
TSX712IYST ⁽²⁾		MiniSO8		K212

Notes:

⁽¹⁾Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 & Q 002 or equivalent are on-going.

⁽²⁾Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 & Q 002 or equivalent.

8 Revision history

Table 10: Document revision history

Date	Revision	Changes
27-Feb-2014	1	Initial release
19-Mar-2014	2	Table 1: updated ESD data for MM (machine model)
25-Jul-2014	3	Table 3: updated I_{out} (I_{sink}) values. Table 3, Table 4, and Table 5: updated V_{io} values, updated $\Delta V_{io}/\Delta T$. Table 5: updated V_{OL} values Table 6: updated "inches" dimensions
26-Jan-2016	4	TSX711 datasheet merged with TSX712 datasheet. Reworked the following sections: Cover image , Related products , Description , Section 1: "Package pin connections" , Section 2: "Absolute maximum ratings and operating conditions" , Section 3: "Electrical characteristics" , Section 4: "Electrical characteristic curves" , Section 5.1: "Operating voltages" , Section 5.2: "Input pin voltage ranges" , Section 5.3: "Rail-to-rail input" , Section 5.4: "Rail-to-rail output" , Section 5.5: "Input offset voltage drift over temperature" , Section 5.7: "High values of input differential voltage" , Section 5.11.1: "Oxygen sensor" , Section 5.11.2: "Low-side current sensing" , Section 7: "Ordering information" . Added: Section 6.2: "MiniSO8 package information" and Section 6.3: "SO8 package information"

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